

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,147,715 B2
APPLICATION NO. : 10/628189
DATED : December 12, 2006
INVENTOR(S) : David Phillip Malta et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page

In the title page under OTHER PUBLICATIONS:

Please add: --J.R. JENNY, ST. G. MULLER, A. POWELL, V.F. TSVETKOV, H.MCD.
HOBGOOD, R.C. GLASS, & C.H.CARTER; High Purity Semi-Insulating 4H-SiC
Grown by the Seeded Sublimation Method; Preprint-2001 Electronic Materials
Conference-submitted to Journal of Electronic Materials, U.S.A--

In the SPECIFICATION

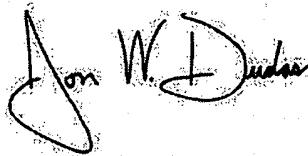
1. Column 6, line 24, delete "modem" and insert therefor -- "modern" --

In the CLAIMS

1. Column 12, line 6, delete "front" and insert therefor -- "from" --
2. Column 12, line 37, delete "send-insulating" and insert therefor -- "semi-insulating" --
3. Column 14, line 6, delete "15K" and insert therefor -- "15R" --

Signed and Sealed this

Twentieth Day of February, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office